

Notice of References Cited	Application/Control No. 10/730,892	Applicant(s)/Patent Under Reexamination SAENGER ET AL.	
	Examiner Scott Geyer	Art Unit 2812	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-2003/0104706	06-2003	Mitsubishi et al.	438/756
*	B	US-2004/0038538	02-2004	Ho et al.	438/694
	C	US-			
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	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Morisaki et al. (Ultra-thin (Teffinv = 1.7nm Poly-Si-gated SiN/HfO2/SiON High-k Stack Dielectrics with High Thermal Stability (1050 degrees C)), ELECTRON DEVICES MEETING, 2002. IEDM '02. DIGEST. INTERNATIONAL, December 8-11, 2002, pages 861-864.
	V	Ng et al. (Electrical Characteristics of Novel Hafnium Oxide Film), 2002, pages 51-54.
	W	Zhan et al. (Characteristics of High Quality Hafnium Oxide gate Dielectric), 2002, pages 43-46
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.